

In claim 38, second line thereof, please insert the degree symbol --°-- between "400" and "C".

40. (Amended) A method of making a mesoporous film on a substrate, the method comprising the steps of:

(a) combining a silica precursor with an aqueous solvent, a catalyst and a surfactant into a precursor solution;

(b) [depositing said precursor solution in the form of a film onto the substrate; and] dispensing said precursor solution on the substrate;

(c) [removing the aqueous solvent, said catalyst and said surfactant from the film to form a mesoporous film, said removing being performed by any one or more of the steps including spin-coating, rapid evaporation and calcination] forming a film by rapid evaporation of the solution on the substrate; and

(d) heating the film on the substrate to a temperature sufficient to decompose the surfactant, thereby producing a mesoporous film on the substrate.

49. (Amended) The method of claim 42, wherein [the precursor solution comprises tetraethoxysilane to form a silica thin film on the substrate], to form a silica thin film on the substrate, the precursor solution contains tetraethoxysilane.

In claim 54, second line thereof, delete "low-k".

In claim 55, second line thereof, after "the mesoporous film is a low-k dielectric film" insert --having a dielectric constant of less than approximately 2.5--. *NE R121*

In claim 56, twelfth and thirteenth lines thereof, change "ration" to --ratio-- (two instances).

Please add the following new claims 63-71:

--63. The method of claim 42 wherein the mesoporous film has sufficient porosity to result in a low-k dielectric constant of less than approximately 2.5. *new matter*

64. A process to form mesostructured films, comprising:

(a) preparing a precursor sol containing a soluble source of a metal oxide, water, an organic solvent, surfactant, and an acid or base catalyst, and

(b) depositing the precursor sol on a substrate wherein evaporation of solvent and water causes the formation of said mesostructured films on the substrate surface wherein said mesostructured films are identified by XRD peaks in the range  $2\theta$ -2°-6° hexagonal, cubic, or lamellar electron diffraction patterns.